

SOT23-6

Complementary Enhancement MOSFET in a SOT23-6 Plastic Package.

N-channel

$V_{DS}(V)=30V$

$I_D=2.7A$

$R_{DS(ON)}@10V<80m\Omega$ (TYP. 66 m Ω)

$R_{DS(ON)}@4.5V<130m\Omega$ (TYP. 95 m Ω)

HF Product.

P-channel

$V_{DS}(V)=-30V$

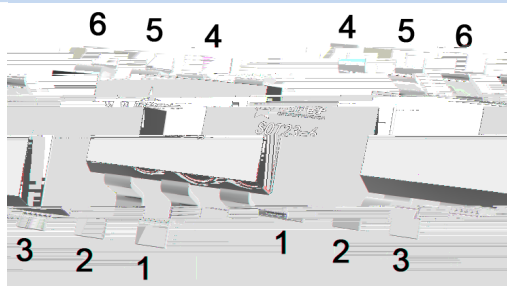
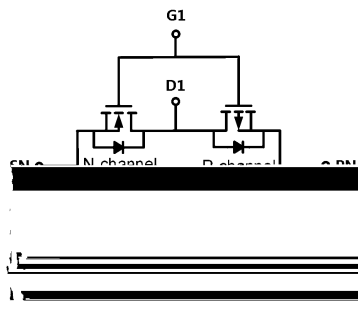
$I_D=-2.6A$

$R_{DS(ON)}@-10V<95 m\Omega$ (TYP. 75 m Ω)

$R_{DS(ON)}@-4.5V<150 m\Omega$ (TYP. 88 m Ω)

PWM

PWM applications, Load switch.

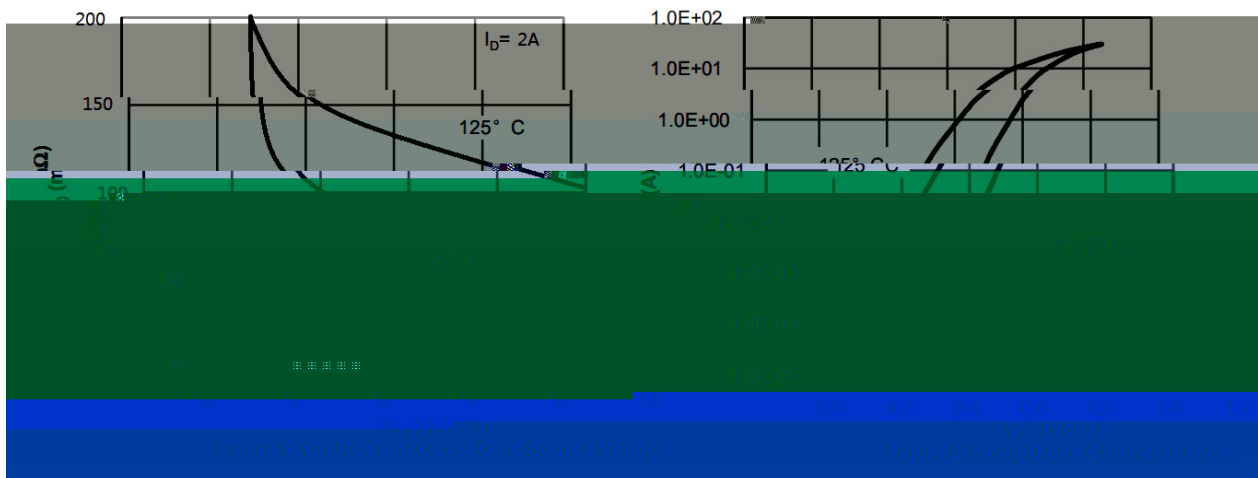
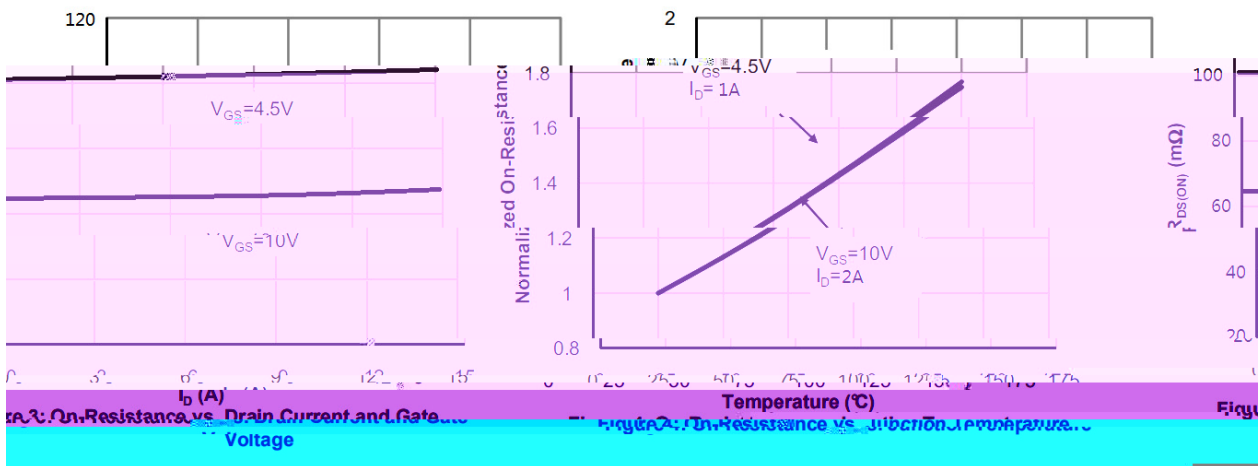


PIN1	G1	PIN 2	SN	PIN 3	G2
PIN 4	D2	PIN 5	SP	PIN 6	D1

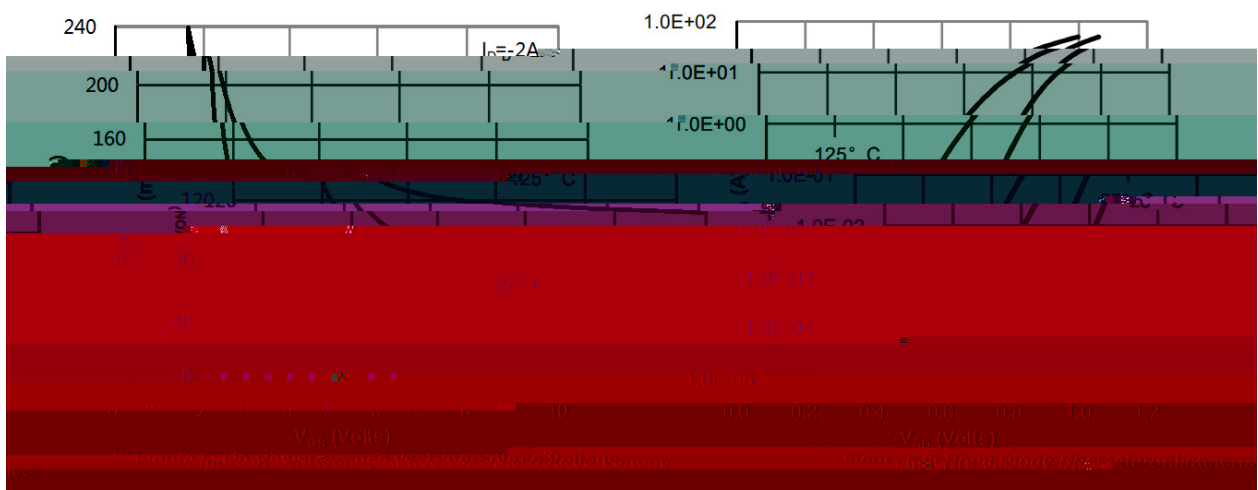
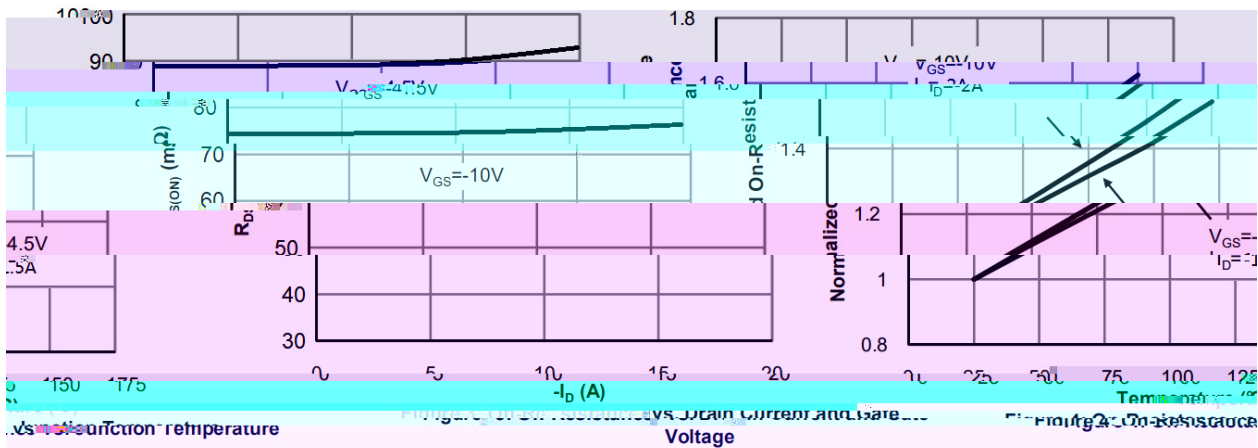
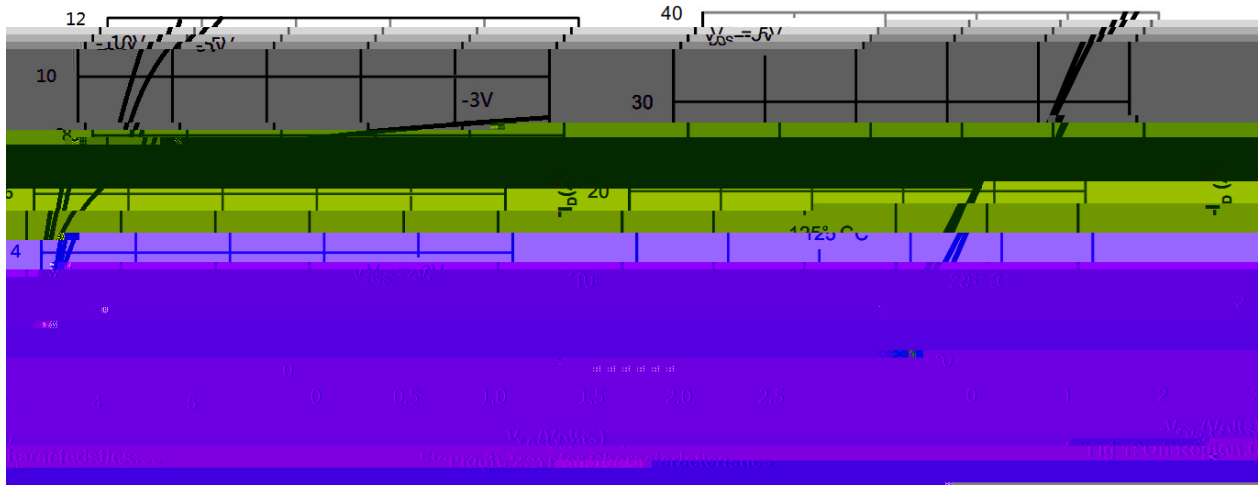
See Marking Instructions.

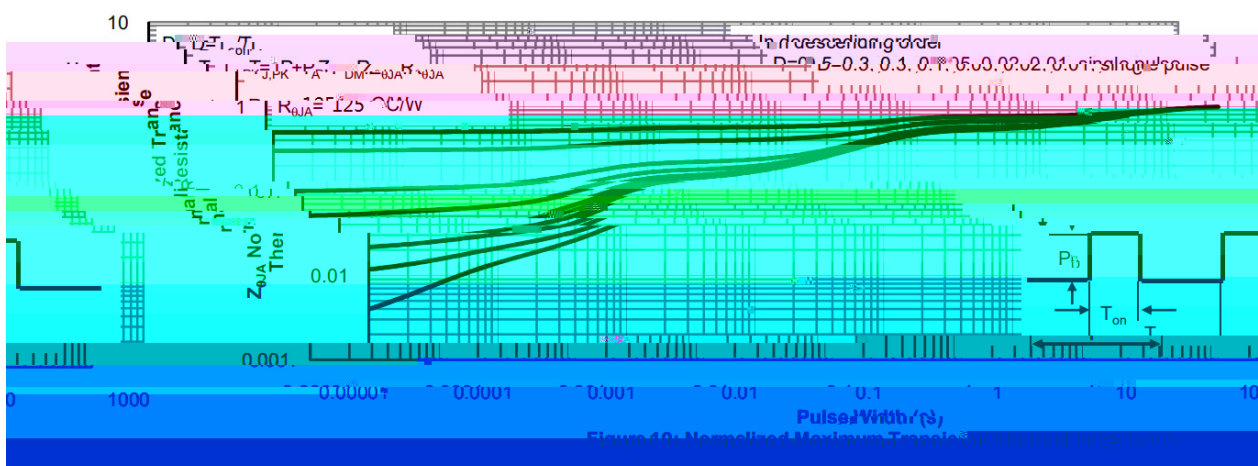
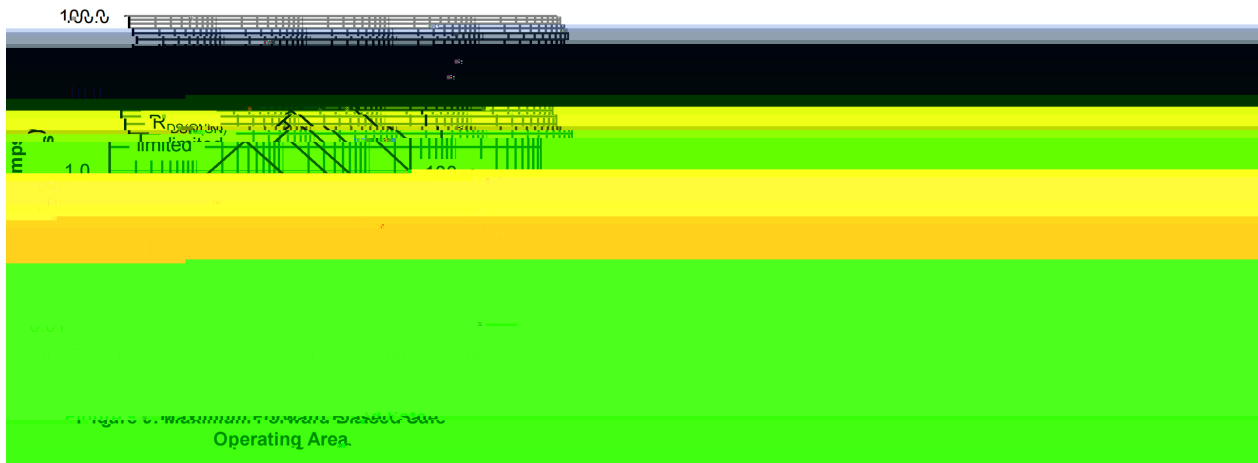
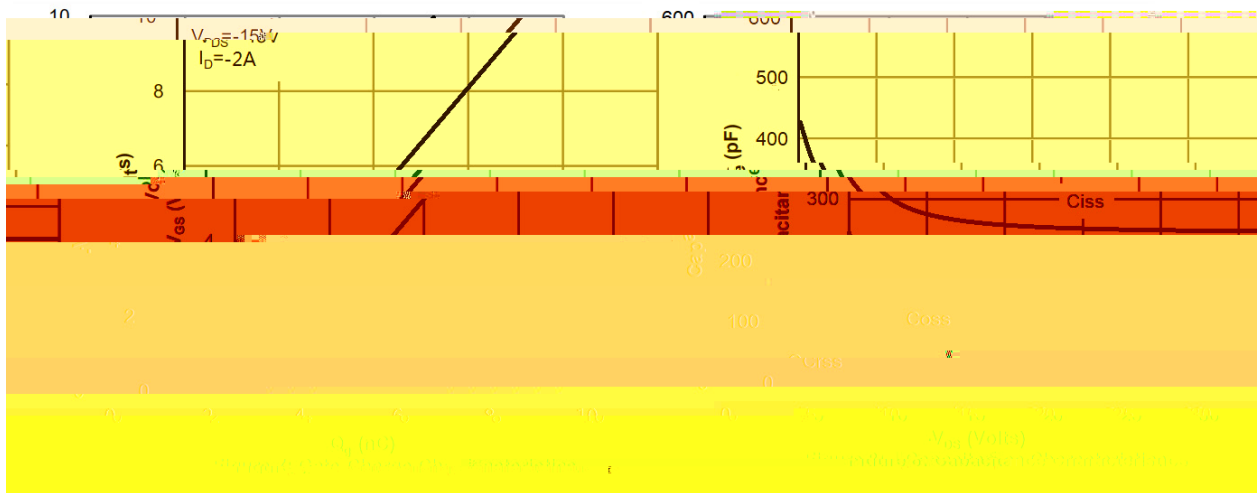
Parameter	Symbol	Rating		Unit
		N-channel	P-channel	
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20		V
Continuous Drain Current	I_D	2.7	-2.6	A
Pulsed Drain Current	I_{DM}	7	-7	A
Power Dissipation	P_D	1		W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150		
Maximum Junction-to-Ambient	$R_{\theta JA}$	125		/W

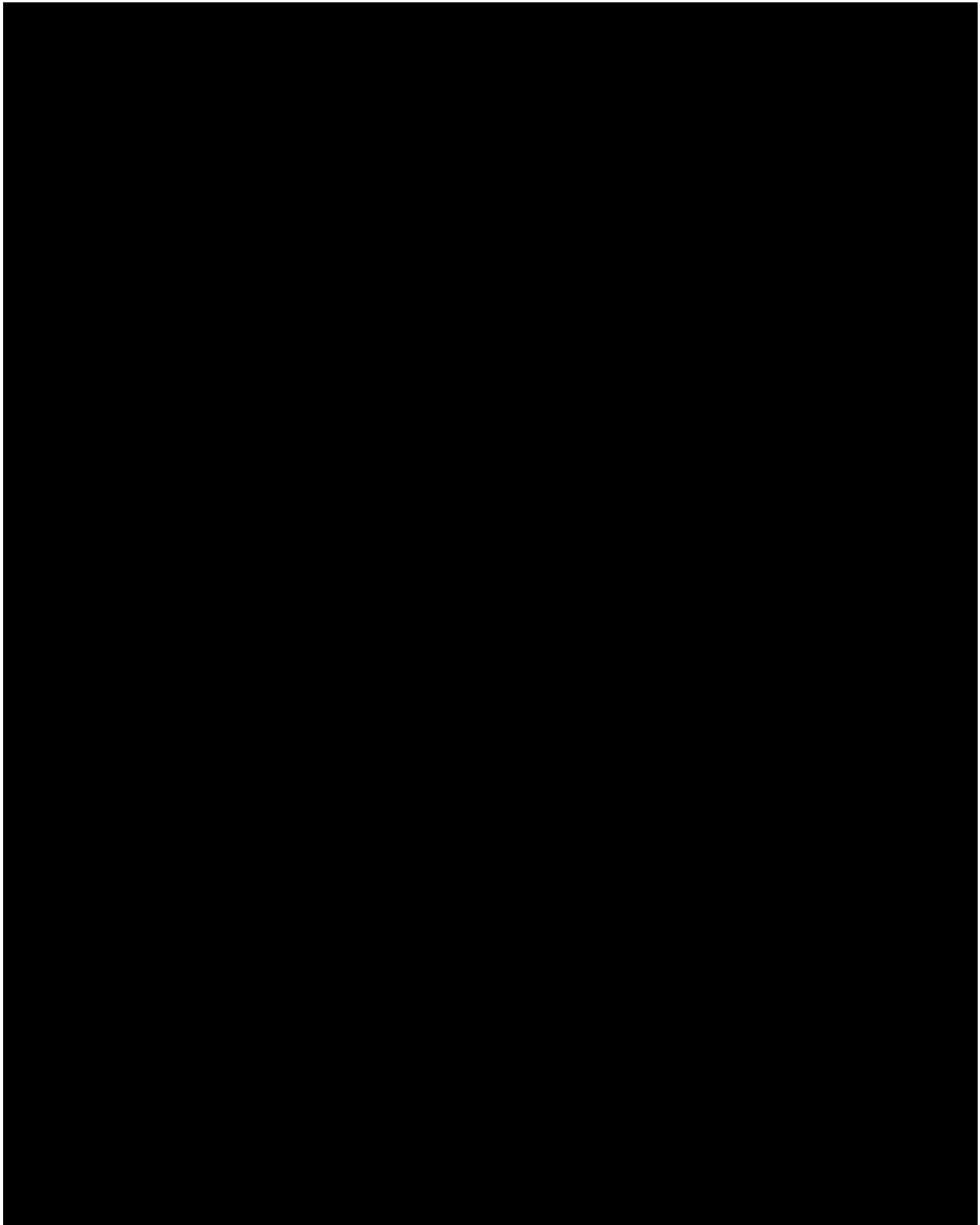
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0$ $I_D=250\mu A$	30	31.5		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0$ $V_{DS}=24V$			1.0	μA
Gate-Body Leakage.	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Static Drain-Source On-Resistance	$R_{DS(on)1}$	$V_{GS}=10V$ $I_D=2.0A$		66	80	m Ω
	$R_{DS(on)2}$	$V_{GS}=4.5V$ $I_D=1.0A$		95	130	m Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_D=1.0A$			1.2	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.45	2.0	V
Input Capacitance	C_{iss}	$V_{DS}=15V$ $f=1.0MHz$ $V_{GS}=0V$		200		pF
Output Capacitance	C_{oss}			30		pF
Reverse Transfer Capacitance	C_{rss}			20		pF
Total Gate Charge	Q_g	$V_{GS}=10V$ $I_D=2A$ $V_{DS}=15V$		5		nC
Gate Source Charge	Q_{gs}			0.8		
Gate Drain Charge	Q_{gd}			1.7		

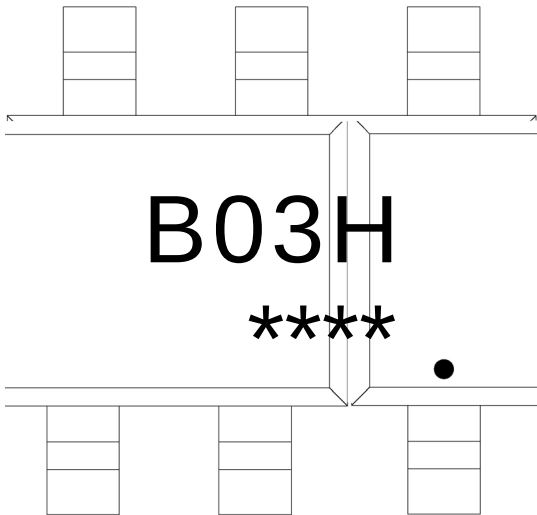


Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V$ $I_D=-250\mu A$	-30	-31.5		V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu A$	-0.5	-0.85	-2.0	V
Static Drain–Source On–Resistance	$R_{DS(on)}$	$V_{GS}=-10V$ $I_D=-2 A$		75	95	m Ω









B03:

H

Note:

B03 Product Type Code

H Company Code

***** Lot No.Code,code change with Lot No

Temperature Profile for IR Reflow Soldering(Pb-Free)

- Note:
- 1

150 180

60 90sec;

2

245±5

5±0.5sec;
- 3

1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.